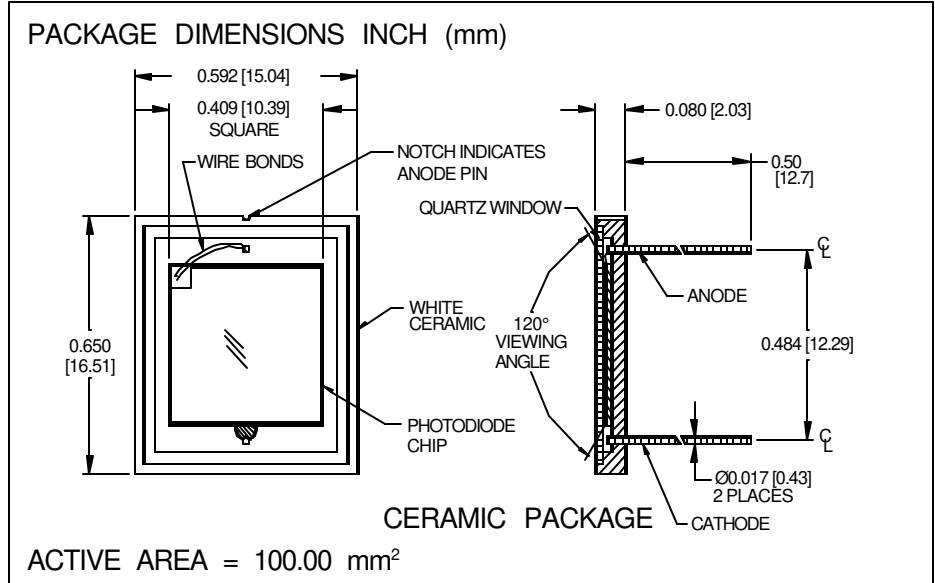
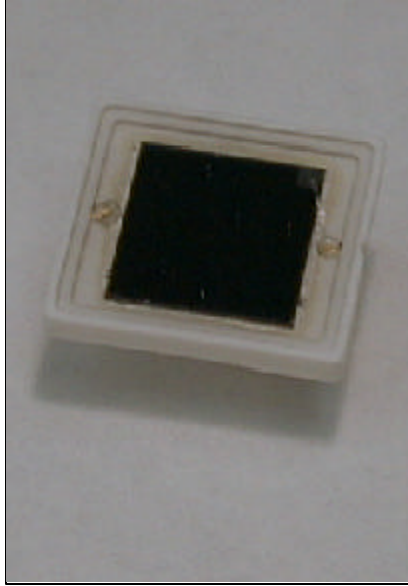


PHOTONIC DETECTORS INC.

Silicon Photodiode, U.V. Enhanced Photoconductive Type PDU-C110-Q



FEATURES

- High speed
- U.V. enhanced
- Low capacitance
- Quartz window

DESCRIPTION

The **PDU-C110-Q** is a silicon, PIN planar diffused, U.V. enhanced photodiode. Ideal for high speed photoconductive applications. Packaged in low profile ceramic substrate with a flat quartz window.

APPLICATIONS

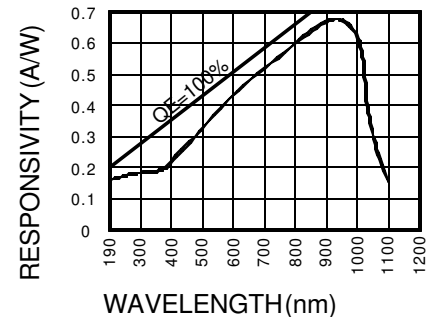
- Spectrometers
- Fluorescent analysers
- U.V. meters
- Colorimeters

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		30	V
T _{STG}	Storage Temperature	-20	+80	°C
T _O	Operating Temperature Range	-20	+60	°C
T _S	Soldering Temperature*		+220	°C
I _L	Light Current		500	mA

*1/16 inch from case for 3 secs max

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{SC}	Short Circuit Current	H = 100 fc, 2850 K	1.0	1.3		mA
I _D	Dark Current	H = 0, V _R = 5 V		10	30	nA
R _{SH}	Shunt Resistance	H = 0, V _R = 10 mV	7	15		MΩ
TC R _{SH}	R _{SH} Temp. Coefficient	H = 0, V _R = 10 mV		-8		% / °C
C _J	Junction Capacitance	H = 0, V _R = 5 V**		600		pF
λ _{range}	Spectral Application Range	Spot Scan	190		1100	nm
R	Responsivity	V _R = 0 V, λ = 254 nm	.12	.18		A/W
V _{BR}	Breakdown Voltage	I = 10 μA	15	25		V
NEP	Noise Equivalent Power	V _R = 10 mV @ Peak		1.5x10 ⁻¹³		W/√Hz
tr	Response Time	R _L = 1 KΩ V _R = 5 V		350		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.**f = 1 MHz

[FORM NO. 100-PDU-C110-Q REV N/C]